

Heating of Two-Dimensional Holes in SiGe and the $B = 0$ Metal-Insulator Transition

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We study the resistivity vs. electric field dependence $\rho(E)$ of a 2D hole system in SiGe close to the $B = 0$ metal-insulator transition. Using ρ as a “thermometer” to obtain the effective temperature of the holes $T_e(E)$, we find that the $\rho(E)$ dependence can be attributed to hole heating. The hole-phonon coupling involves weakly screened piezoelectric and deformation potentials compatible with previous measurements. The damping of the Shubnikov-de Haas oscillations gives the same T_e values. Thus the $\rho(E)$ dependence and the E -field “scaling” do not provide additional evidence for a quantum phase transition (QPT). We discuss how to study, in general, true E -field scaling and extract the ratio of the QPT characteristic lengths.

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The recent observations of a metal-insulator transition (MIT) in two-dimensional (2D) electron or hole systems in high mobility silicon metal-oxide-semiconductor field effect transistors (Si-MOSFETs) [1,2] and in certain heterostructures [3–8] have triggered important experimental and theoretical efforts to understand the unexpected metallic behavior [8,9]. This consists in a decrease of the resistivity ρ for decreasing temperature T , at densities p_s larger than the critical density p_c . In contrast, $d\rho/dT < 0$ on the insulating side of the MIT ($p_s < p_c$). The extrapolated finite resistivity at $T=0$ is in conflict with the scaling theory of localization for non-interacting particles which predicts localized states in 2D systems [10]. The MIT occurs for values of r_s (the ratio of a carrier pair Coulomb energy to the Fermi energy) much larger than one, suggesting the existence of a non-Fermi liquid due to strong interactions. The MIT could thus be the signature of a $T=0$ quantum phase transition (QPT) between new metallic and insulating phases. However, for some systems, e.g. p -SiGe, it seems that the positive $d\rho/dT$ is due to quasi-classical processes masking the usual weak localization which should appear again at low enough temperatures [9,11–13]. At present, the nature of the MIT is still a subject of ongoing discussions.

A striking feature of the MIT is that at low temperature, the dependence of ρ as a function of the electric field E is similar to $\rho(T)$, i.e. $d\rho/dE < 0$ for $p_s < p_c$ and $d\rho/dE > 0$ for $p_s > p_c$ [4,7,14–17]. The physical origin of this observation is an open question. Irrespective of the possible microscopic explanations of the $\rho(E, p_s)$ dependence [14,18], a QPT implies that ρ scales with E if it scales with T [19]: close to the critical point, two characteristic length scales are associated with T and E , $L_\Phi(T) \sim T^{-1/z}$ and $L_E(E) \sim E^{-1/(z+1)}$, and ρ depends only on the ratio of the smallest of them to the correlation length $\xi \sim |\delta_n|^{-\nu}$ (z is the dynamical exponent, ν

the correlation length exponent, and $\delta_n = (p_s - p_c)/p_c$). Thus $\rho(T, p_s)$ (for $E \rightarrow 0$) depends only on $|\delta_n|/T^{1/z\nu}$ on each side of the transition, and $\rho(E, p_s)$ (at low temperature) depends only on $|\delta_n|/E^{1/(z+1)\nu}$. The scaling analysis of $\rho(T, p_s)$ and $\rho(E, p_s)$ allows a separate extraction of z and ν . E scaling has been observed in several systems exhibiting T scaling [7,15–17]. However, a natural question is whether the $\rho(E)$ dependence results from carrier heating [19]. At low temperature, the weak carrier-phonon coupling can lead to an effective temperature of the carriers, $T_e(E)$, larger than the lattice temperature T_l [9,20–28]. Thus, the $\rho(E)$ dependence can be due to the $T_e(E)$ dependence of ρ .

In this paper, we demonstrate experimentally that for a 2D hole system in p -SiGe exhibiting the MIT features with T and E scaling, the resistivity vs. E -field dependence can be attributed to hole heating. We find $\rho(E, p_s) = \rho(T = T_e(E), p_s)$ with a law $T_e(E)$ compatible both in shape and magnitude with known electron-phonon coupling models and data. The same $T_e(E)$ is obtained from the damping of the Shubnikov-de Haas (SdH) oscillations. Thus, in the present case, the $\rho(E, p_s)$ dependencies and the E -field “scaling” are not arguments in favor of the QPT interpretation of the “MIT” and the separate extraction of ν and z is not possible. As heating effects depend on the semiconductor structure, while E scaling is a crucial issue for the QPT, we discuss the conditions required to study it for various systems in spite of carrier heating. We show how the ratio L_Φ/L_E can be obtained experimentally.

The experiments were performed on $\text{Si}_{0.85}\text{Ge}_{0.15}$ quantum wells sandwiched between undoped Si layers [7,12]. The 2D hole gas was formed in the triangular potential well at the Si/SiGe interface located on the boron doped side. It occupies the lowest heavy-hole subband, with an effective mass of about $0.25m_0$. Two gated Hall bars (S1

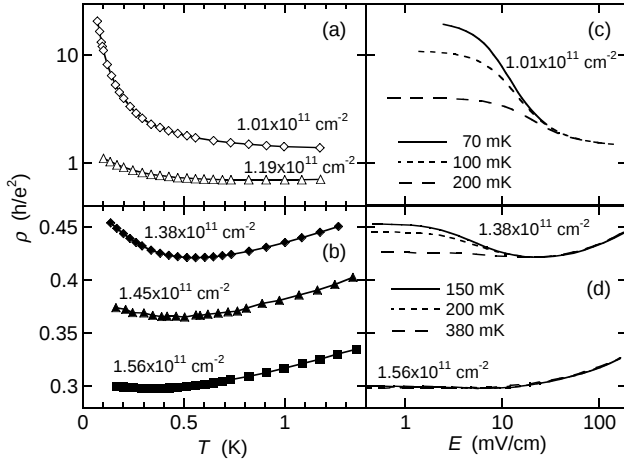


FIG. 1. (a)-(b) Resistivity as a function of temperature (for $E \rightarrow 0$), at different densities for sample S1. (c)-(d) Resistivity as a function of electric field for various densities and lattice temperatures.

and S2) were used. Their width W is $100 \mu\text{m}$, and their length L (between voltage probes) $233 \mu\text{m}$ for S1, and $125 \mu\text{m}$ for S2. By varying the gate voltage, their densities can be tuned between 0.50 and $1.75 \times 10^{11} \text{ cm}^{-2}$. The mobilities at 200 mK increase with p_s from 600 to $5500 \text{ cm}^2/\text{Vs}$ (resp. 1000 to $7400 \text{ cm}^2/\text{Vs}$) for S1 (resp. S2). An ungated sample, with a density of $3.9 \times 10^{11} \text{ cm}^{-2}$ and a mobility of $7800 \text{ cm}^2/\text{Vs}$ has also been used. The temperature range was $70 \text{ mK} - 1.4 \text{ K}$. To check that the temperature T given by the thermometer fixed in the copper sample holder was that of the lattice T_l , the low current resistance of another Hall bar etched onto the same substrate was used as a thermometer. Its temperature remained close to T whatever the current in our samples. $\rho = (V/I)(W/L)$ and $E = V/L$ were obtained from the current I and the voltage drop V between the voltage probes, using a four point DC technique, with a current ($10 - 300 \text{ pA}$ for low E measurements) periodically reversed at a frequency $0.03 - 0.3 \text{ Hz}$.

The MIT features appear in the $\rho(T, p_s)$ dependence for $E \rightarrow 0$ [Fig. 1(a)-(b)]. $d\rho/dT < 0$ is found for $p_s < p_c \approx 1.3 \times 10^{11} \text{ cm}^{-2}$ ($r_s \approx 6$), while $d\rho/dT > 0$ for $p_s > p_c$, at temperatures above a threshold which decreases when p_s increases. At the largest densities $d\rho/dT$ is positive. The $\rho(T, p_s)$ data plotted as a function of $|\delta_n|/T^b$ for $T > 0.3 - 0.5 \text{ K}$ collapse on two branches (not shown), demonstrating a scaling behavior with $b = 0.45 \pm 0.04$. The values 0.35 [7] and 0.62 [5,6] were found in p -SiGe. The MIT characteristics and E -field scaling appear also in the $\rho(E, p_s)$ curves (Fig. 2), p_c remaining unchanged. When ρ is plotted as a function of $|\delta_n|/E^a$ ($a = 0.19 \pm 0.02$), the curves fall on two branches (inset of Fig. 2). They contain only a part of the data (symbols on Fig. 2): removing the low E points is justified by $L_E < L_\Phi$ (assuming a real QPT), while for

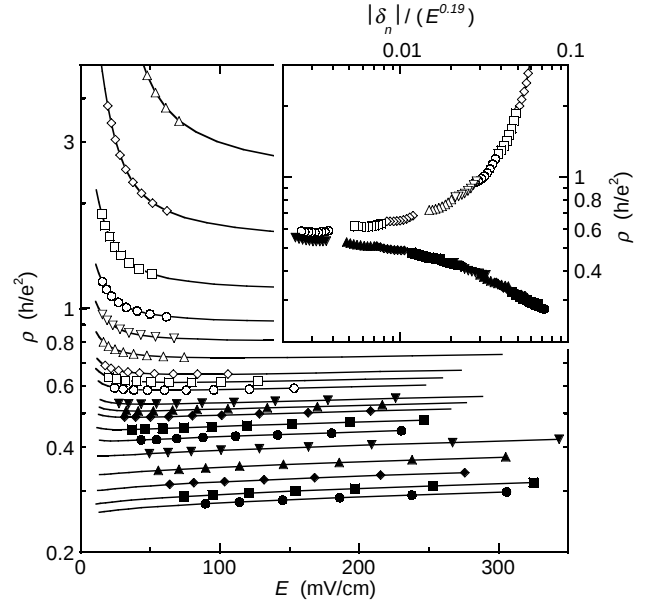


FIG. 2. Resistivity of sample S1 as a function of electric field at various hole densities: from $p_s = 0.92 \times 10^{11} \text{ cm}^{-2}$ (top curve), to $p_s = 1.75 \times 10^{11} \text{ cm}^{-2}$ (bottom curve). The lattice temperature is 120 mK . The lines give the whole set of data for $E > 10 \text{ mV/cm}$, while the symbols correspond to the fraction of the data used in the curves presented in the inset. Inset: resistivity as a function of $|\delta_n|/E^{0.19}$.

large E , it can be related to a microscopic limit on L_E .

Figure 1 shows that the general shape and the minima of $\rho(E)$ are the same as those of $\rho(T)$, suggesting hot hole effects. Their contribution is studied as follows: (i) the $\rho(E)$ dependence is assumed to result from the hole temperature rise from T_l to T_e due to Joule heating; (ii) for each value of E , ρ is used as a “thermometer” giving T_e as the temperature T at which the same value of ρ is measured for $E \rightarrow 0$; (iii) the relationship between T_e and the power per carrier $P_E = VI/(p_s WL) = E^2/(\rho p_s)$ is used to study the validity of the hot carrier assumption (i). Figure 3(a) shows the $P_E(T_e)$ dependence for various lattice temperatures and for densities around p_c .

The power loss between a degenerate 2D electron system and the lattice 3D acoustic phonons is given by [20]

$$P_E = A(T_e^\alpha - T_l^\alpha) + A'(T_e^{\alpha'} - T_l^{\alpha'}). \quad (1)$$

The first term corresponds to the deformation potential coupling, with $\alpha = 5$ (resp. 7) for weak (resp. strong) screening. The second term is piezoelectric coupling, to be considered for our coherently strained SiGe samples [21,29], with $\alpha' = 3$ (resp. 5) for weak (resp. strong) screening. The exponents may be decreased by one in disordered systems because of “dynamic” rather than “static” screening [23]. A and A' are prefactors related to the deformation (Ξ_u) and piezoelectric (e_{pz}) coupling constants [20,21]. To test the validity of Eq. (1) for our measurements, we write it: $P_E + (AT_l^\alpha + A'T_l^{\alpha'}) =$

$(AT_e^\alpha + A'T_e^{\alpha'})$. Figure 3(b) shows that by adding to P_E a constant $P_0(T_l)$ chosen separately for each T_l , the whole set of curves for a given density falls on the same master curve. Hence $P_E(T_e, T_l) + P_0(T_l)$ depends only on T_e , and this dependence is the sum of two power laws. We have verified that the $P_0(T_l)$ dependence is *the same*, thus proving that our data are in agreement with Eq. (1). Similar results are obtained for all densities and samples. For p_s close to p_c , a power law with $\alpha' \approx 3$ (resp. $\alpha \approx 5 - 6$) dominates at low (resp. large) T_e . These power laws are confirmed by fitting the $P_E(T_e)$ data with Eq. (1). Fig. 3(a) shows the good quality of the fit when $\alpha = 5$ and $\alpha' = 3$ are imposed. For $p_s > 1.35 \times 10^{11} \text{ cm}^{-2}$, a term $A''(T_e^2 - T_l^2)$ is added in the fit, corresponding to the cooling through the contacts which increases when ρ decreases [24]. A'' has the same order of magnitude as the value given by the Wiedeman-Franz law. Our data are thus compatible with Eq. (1), the two main cooling processes being hole-phonon coupling through weakly screened deformation and piezoelectric potentials. Weak screening at low temperatures has been pointed out in p -SiGe [21,26] and Si-MOSFETs [24,25]. A and A' are obtained from a fit with Eq. (1) assuming $\alpha = 5$ and $\alpha' = 3$ [Fig. 3(a)]. Following Ref. [21] we then obtain $\Xi_u = 2.7 \pm 0.3 \text{ eV}$ and $e_{pz} = (3.4 \pm 0.9) \times 10^{-3} \text{ C/m}^2$ for all the densities. Our Ξ_u value is compatible with the $\Xi_u \approx 3.0 \text{ eV}$ found in p -SiGe at $p_s = (3.5 - 13) \times 10^{11} \text{ cm}^{-2}$ [21,26]. Our e_{pz} is somewhat lower than the $e_{pz} \approx 1.6 \times 10^{-2} \text{ C/m}^2$ obtained in p -Si_{0.8}Ge_{0.2} [21], however in Ref. [26] e_{pz} was found to be much smaller than in Ref. [21].

In order to further prove the validity of the heating analysis, the T_e extracted at $B = 0$ is compared to the temperature obtained using the damping of the SdH oscillations [21,22,24,27]. To get rid of the $\rho_{xx}(T)$ dependence due to carrier scattering [27], the “thermometer” is the difference between a minimum of $\rho_{xx}(B)$ and the previous maximum. Its T dependence results from a different physical situation (the density of states oscillations) than at $B = 0$. The magnetic field values ($B \approx 1 \text{ T}$) are low to ensure that the electron-phonon coupling laws extracted are close to those at $B = 0$ [27]. As shown in the inset of Fig. 3(a) for $p_s = 1.19 \times 10^{11} \text{ cm}^{-2}$ and $T_l = 150 \text{ mK}$, the two methods are in very good agreement. A similar agreement is obtained for other T_l values and for $p_s = 3.9 \times 10^{11} \text{ cm}^{-2}$. Thus, the $\rho(E)$ dependence can be attributed to hole heating, implying that it does not bring new physical information on the possible MIT when compared to the $\rho(T)$ dependence.

To study E -field scaling in spite of heating effects, the condition $L_E(E) < L_\Phi[T_e(E)]$ must be fulfilled. Figure 4 shows how L_Φ and L_E depend on E . The vertical scale is arbitrary because L_Φ and L_E are not given by the QPT theory, but assuming $z = 1$ for strongly interacting particles [19], $L_\Phi \sim T^{-1}$ and $L_E \sim E^{-1/2}$. Although the “metallic” $\rho(T)$ in our samples is compatible with

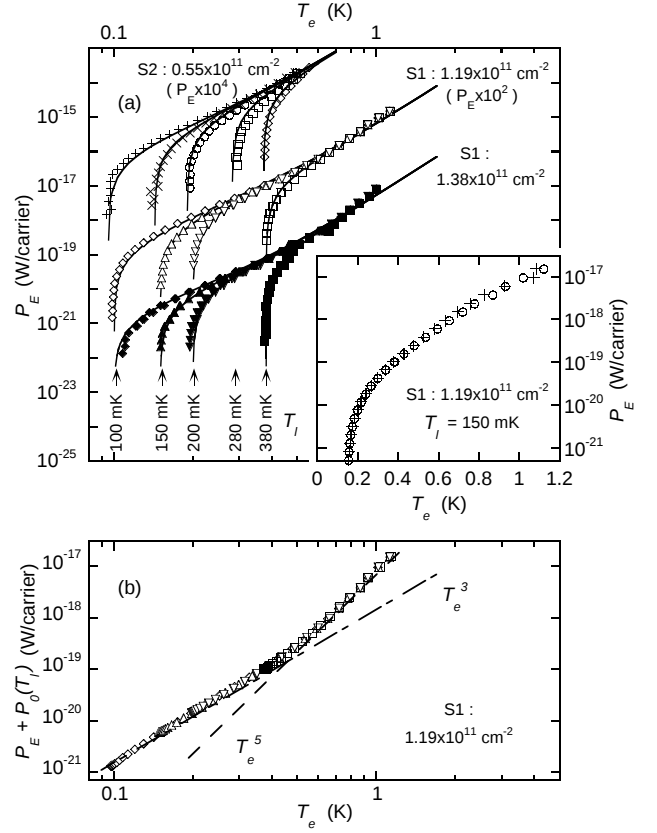


FIG. 3. (a) Power per hole injected in the 2D system as a function of the holes effective temperature, for two gated samples and three densities, at several lattice temperatures (arrows). For clarity, the curves corresponding to $p_s = 1.19 \times 10^{11} \text{ cm}^{-2}$ (resp. to $p_s = 0.55 \times 10^{11} \text{ cm}^{-2}$) are shifted upwards by 100 (resp. by 10^4). The lines corresponding to the two lower densities are fits to $P_E = A(T_e^5 - T_l^5) + A'(T_e^3 - T_l^3)$; while for the larger density a third term $A''(T_e^2 - T_l^2)$ has been added in the fit formula. Inset: P_E as a function of the effective temperature extracted using the ρ thermometer at $B = 0$ (o) or the damping of the SdH oscillations (+). (b) The sum of the power per hole and a constant $P_0(T_l)$ chosen for each T_l , as a function of the hole effective temperature, for various lattice temperatures $T_l = 100 \text{ mK}$ ($\diamond$), 150 mK ($\triangle$), 200 mK (∇), and 380 mK ($\square$). The lines give the slopes of the power laws T_e^3 and T_e^5 .

a Fermi liquid description [12], it is instructive to consider the possibility of a QPT: the full line corresponds to $L_\Phi[T_e(E)]$ in our case, for $p_s \approx p_c$, using the experimental law $T_e(E)$, obtained in the E interval indicated by the symbols. An upper limit for E arises since the longitudinal potential drop $V = EL$ has to be kept small compared to the gate voltage. As we attributed the measured $\rho(E)$ dependence to heating, the $L_E(E)$ line (long dashed) crosses the $L_\Phi[T_e(E)]$ curve beyond this interval. The E -field scaling can be investigated only beyond this crossing point, (“ E scaling” interval in Fig. 4), provided L_Φ and L_E do not reach their microscopic limit.

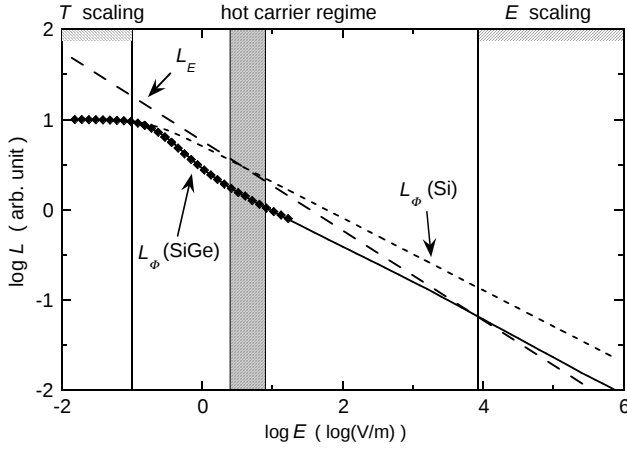


FIG. 4. The logarithm of L_Φ and L_E as a function of the electric field. The full line represents $L_\Phi[T_e(E)]$ calculated using Eq. (1) at $p_s = 1.31 \times 10^{11} \text{ cm}^{-2}$ and $T_l = 100 \text{ mK}$. The symbols correspond to our experimental points. Short-dashed line: $L_\Phi[T_e(E)]$ estimated for Si-MOSFETs close to the MIT. Long-dashed line: $L_E(E)$ assumed to be the same for SiGe heterostructures and Si-MOSFETs. The vertical lines separate the hot carrier region from the T and E scaling regions for p -SiGe. The grey area gives the limits above which the E -field scaling is improved in Ref. [17]

The short dashed line in Fig. 4 is $L_\Phi[T_e(E)]$ for Si-MOSFETs, estimated using recent measurements of the power loss [24,30]. Again, the $L_E(E) < L_\Phi[T_e(E)]$ prescription leads to a lower limit for E . This agrees with the results of Ref. [17] where the quality of the E -field scaling is improved when E is larger than a minimum value (the grey area in Fig. 4, corresponds to their cut-offs of 50 to 500 pW). For p -GaAs, the $\alpha = 5$ exponent quoted in Ref. [28] leads to a similar situation, but the thermal coupling should be larger than in Si-MOSFETs. Unscreened piezoelectric coupling would lead to an upper E -field limit. A better knowledge of the power loss laws would allow a quantitative use of the $L_E(E) < L_\Phi(T_e)$ prescription. The field E_c defined by $L_E(E_c) = L_\Phi[T_e(E_c)]$ could be extracted as the limit beyond which the experimental $P_E(T_e)$ law differs from the power loss law, thus yielding the important physical result $L_\Phi(T)/L_E(E) = [T_e(E_c)/T]^{1/z}(E/E_c)^{1/(z+1)}$.

The ratio of the exponents in the experimental scaling laws $\rho(|\delta_n|/T^b)$ and $\rho(|\delta_n|/E^a)$ has been proposed as an indicator of the $\rho(E)$ dependence origin [19]. For the QPT scaling, $a/b = z/(z+1) = 0.5$. For carrier heating, Eq. (1) gives $T_e \sim (E^{2/\alpha})\rho^{-1/\alpha}$, thus $a/b = 2/\alpha$ neglecting A' , T_l and the $\rho(T)$ dependence. We find experimentally $a/b = 0.42 \pm 0.08$, while 0.4 and 0.67 are expected for our α and α' , thus the a/b criterion can hardly be used [31].

In summary, we have shown that in a 2D hole system exhibiting the $B = 0$ MIT characteristics, with T and E scaling, the $\rho(E)$ dependence close to the MIT could

be interpreted as being due to hole heating. Thus, in our case, the experimental $\rho(E, p_s)$ and E -field scaling are not an indication that the MIT features can be attributed to a QPT, and the separate extraction of ν and z is not possible. However, there is an E interval defined by $L_E(E) < L_\Phi[T_e(E)]$ where E -field scaling can be investigated independent of hot carrier effects.

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 - [31] Similarly, in Si-MOSFETs, unscreened electron-phonon coupling [24,25] would lead to $2/\alpha = 0.4$.